

KSE200

Feature

- Low Collector-Emitter Saturation Voltage
- High Current Gain Bandwidth Product : f_T =65MHz @ I_C =100mA (Min.)
- Complement to KSE210



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|------------|-------|
| V _{CBO} | Collector-Base Voltage | 40 | V |
| V _{CEO} | Collector-Emitter Voltage | 25 | V |
| V _{EBO} | Emitter- Base Voltage | 8 | V |
| I _C | Collector Current | 5 | Α |
| P _C | Collector Dissipation (T _C =25°C) | 15 | W |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 65 ~ 150 | °C |

Electrical Characteristics $T_C=25$ °C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|-----------------------|--------------------------------------|---|------|------|-------|
| BV _{CEO} | Collector-Emitter Breakdown Voltage | I _C =10mA, I _B =0 | 25 | | V |
| I _{CBO} | Collector Cut-off Current | V _{CB} =40V, I _E =0 | | 100 | nA |
| | | V _{CB} =40V, I _E =0 @ T _J =125°C | | 100 | μΑ |
| I _{EBO} | Emitter Cut-off Current | V_{BE} =8V, I_{C} =0 | | 100 | nA |
| h _{FE} | DC Current Gain | V_{CE} =1V, I_{C} =500mA | 70 | | |
| | | $V_{CE}=1V$, $I_{C}=2A$ | 45 | 180 | |
| | | $V_{CE}=2V$, $I_{C}=5A$ | 10 | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C =500mA, I _B =50mA | | 0.3 | V |
| | | I _C =2A, I _C =200mA | | 0.75 | V |
| | | I _C =5A, I _B =1A | | 1.8 | V |
| V _{BE} (sat) | Base- Emitter Saturation Voltage | I _C =5A, I _B =1A | | 2.5 | V |
| V _{BE} (on) | Base-Emitter On Voltage | V _{CE} =1V, I _C =2A | | 1.6 | V |
| f _T | Current Gain Bandwidth Product | V _{CE} =10V, I _C =100mA | 65 | | MHz |
| C _{ob} | Output Capacitance | V _{CB} =10V, I _E =0, f=0.1MHz | | 80 | pF |

Typical Characteristics

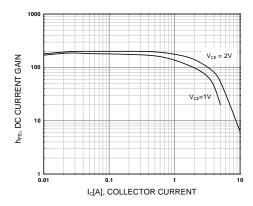


Figure 1. DC current Gain

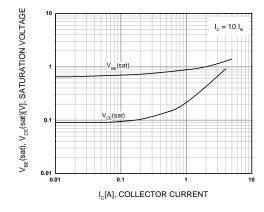


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

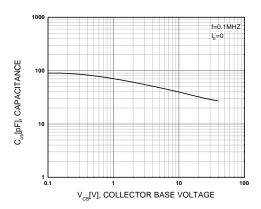


Figure 3. Collector Output Capacitance

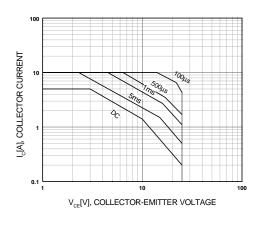


Figure 4. Forward Bias Safe Operating Area

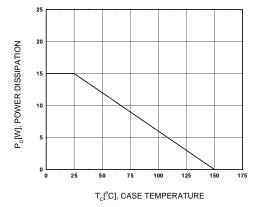
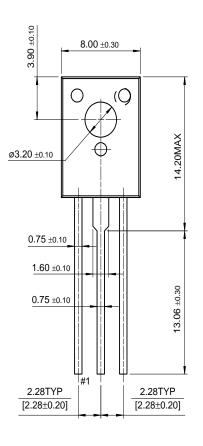
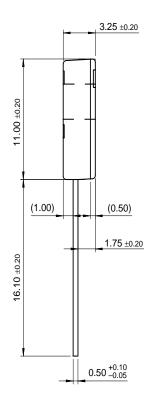


Figure 5. Power Derating

Package Demensions

TO-126







Dimensions in Millimeters

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Rev. H2

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|--------------------------|---------------------------|---|
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